Won Jong Yoo

List of Publications by Year in Descending Order

167 papers	7,078 citations	41 h-index	81 g-index
183 ext. papers	8,269 ext. citations	7.2 avg, IF	5.82 L-index

#	Paper	IF	Citations
167	Anomalously persistent p-type behavior of WSe2 field-effect transistors by oxidized edge-induced Fermi-level pinning. *Journal of Materials Chemistry C*, **2022**, 10, 846-853	7.1	1
166	Edge Rich Ultrathin Layered MoS Nanostructures for Superior Visible Light Photocatalytic Activity.. *Langmuir*, **2022**,	4	1
165	Ultrahigh Anisotropic Transport Properties of Black Phosphorus Field Effect Transistors Realized by Edge Contact. *Advanced Electronic Materials*, **2022**, 8, 2100988	6.4	3
164	Recent progress in 1D contacts for 2D material-based devices.. *Advanced Materials*, **2022**, e2202408	24	1
163	Controlling Carrier Transport in Vertical MoTe/MoS van der Waals Heterostructures. *ACS Applied Materials & Interfaces*, **2021**, 13, 54294-54300	9.5	0
162	High carrier mobility in graphene doped using a monolayer of tungsten oxyselenide. *Nature Electronics*, **2021**, 4, 731-739	28.4	4
161	Damage-Free Atomic Layer Etch of WSe: A Platform for Fabricating Clean Two-Dimensional Devices. *ACS Applied Materials & Interfaces*, **2021**, 13, 1930-1942	9.5	12
160	Electrical characterization of 2D materials-based field-effect transistors. *2D Materials*, **2021**, 8, 012002	5.9	38
159	Resonant tunnelling diodes based on twisted black phosphorus homostructures. *Nature Electronics*, **2021**, 4, 269-276	28.4	9
158	Fermi-Level Pinning Free High-Performance 2D CMOS Inverter Fabricated with Van Der Waals Bottom Contacts. *Advanced Electronic Materials*, **2021**, 7, 2001212	6.4	11
157	Traps at the hBN/WSe2 interface and their impact on polarity transition in WSe2. *2D Materials*, **2021**, 8, 035027	5.9	2
156	Interface state density and barrier height improvement in ammonium sulfide treated Al2O3/Si interfaces. *Current Applied Physics*, **2021**, 26, 83-89	2.6	
155	High performance WSe2 p-MOSFET with intrinsic n-channel based on back-to-back p□ junctions. *Applied Physics Letters*, **2021**, 118, 233101	3.4	8
154	Low-Temperature and Large-Scale Production of a Transition Metal Sulfide Vertical Heterostructure and Its Application for Photodetectors. *ACS Applied Materials & Interfaces*, **2021**, 13, 8710-8717	9.5	10
153	Analytical measurements of contact resistivity in two-dimensional WSe2 field-effect transistors. *2D Materials*, **2021**, 8, 045019	5.9	2
152	Fermi Level Pinning Dependent 2D Semiconductor Devices: Challenges and Prospects.. *Advanced Materials*, **2021**, e2108425	24	10
151	Directly Probing Effective-Mass Anisotropy of Two-Dimensional ReSe2 in Schottky Tunnel Transistors. *Physical Review Applied*, **2020**, 13,	4.3	8

150	Self-Terminated Surface Monolayer Oxidation Induced Robust Degenerate Doping in MoTe for Low Contact Resistance. *ACS Applied Materials & Interfaces*, **2020**, 12, 26586-26592	9.5	14
149	Phase-Engineered Molybdenum Telluride/Black Phosphorus Van der Waals Heterojunctions for Tunable Multivalued Logic. *ACS Applied Materials & Interfaces*, **2020**, 12, 14119-14124	9.5	16
148	High-Electric-Field-Induced Phase Transition and Electrical Breakdown of MoTe2. *Advanced Electronic Materials*, **2020**, 6, 1900964	6.4	15
147	Large-area single-crystal AB-bilayer and ABA-trilayer graphene grown on a Cu/Ni(111) foil. *Nature Nanotechnology*, **2020**, 15, 289-295	28.7	76
146	Gate-Modulated Ultrasensitive Visible and Near-Infrared Photodetection of Oxygen Plasma-Treated WSe Lateral pn-Homojunctions. *ACS Applied Materials & Interfaces*, **2020**, 12, 23261-23271	9.5	19
145	Effect of large work function modulation of MoS2 by controllable chlorine doping using a remote plasma. *Journal of Materials Chemistry C*, **2020**, 8, 1846-1851	7.1	11
144	Charge Density Depinning in Defective MoTe2 Transistor by Oxygen Intercalation. *Advanced Functional Materials*, **2020**, 30, 2004880	15.6	9
143	Control of the Schottky Barrier and Contact Resistance at Metal□WSe2 Interfaces by Polymeric Doping. *Advanced Electronic Materials*, **2020**, 6, 2000616	6.4	10
142	The device level modulation of carrier transport in a 2D WSe field effect transistor via a plasma treatment. *Nanoscale*, **2019**, 11, 17368-17375	7.7	14
141	Metallic contact induced van der Waals gap in a MoS FET. *Nanoscale*, **2019**, 11, 18246-18254	7.7	6
140	Van der Waals Broken-Gap p-n Heterojunction Tunnel Diode Based on Black Phosphorus and Rhenium Disulfide. *ACS Applied Materials & Interfaces*, **2019**, 11, 8266-8275	9.5	29
139	A Fermi-Level-Pinning-Free 1D Electrical Contact at the Intrinsic 2D MoS -Metal Junction. *Advanced Materials*, **2019**, 31, e1808231	24	66
138	Transferred via contacts as a platform for ideal two-dimensional transistors. *Nature Electronics*, **2019**, 2, 187-194	28.4	90
137	Multifunctional van der Waals Broken-Gap Heterojunction. *Small*, **2019**, 15, e1804885	11	42
136	Adlayer-Free Large-Area Single Crystal Graphene Grown on a Cu(111) Foil. *Advanced Materials*, **2019**, 31, e1903615	24	53
135	Ohmic Contact in 2D Semiconductors via the Formation of a Benzyl Viologen Interlayer. *Advanced Functional Materials*, **2019**, 29, 1807338	15.6	15
134	Energy Dissipation in Black Phosphorus Heterostructured Devices. *Advanced Materials Interfaces*, **2019**, 6, 1801528	4.6	9
133	Patterning metal contacts on monolayer MoS2 with vanishing Schottky barriers using thermal nanolithography. *Nature Electronics*, **2019**, 2, 17-25	28.4	73

132	Homogeneous molybdenum disulfide tunnel diode formed via chemical doping. *Applied Physics Letters*, **2018**, 112, 183103	3.4	10
131	Impact ionization by hot carriers in a black phosphorus field effect transistor. *Nature Communications*, **2018**, 9, 3414	17.4	23
130	Dielectric Dispersion and High Field Response of Multilayer Hexagonal Boron Nitride. *Advanced Functional Materials*, **2018**, 28, 1804235	15.6	18
129	Colossal grain growth yields single-crystal metal foils by contact-free annealing. *Science*, **2018**, 362, 1021-1025	33.9	107
128	Ultrahigh Photoresponsive Device Based on ReS /Graphene Heterostructure. *Small*, **2018**, 14, e1802593	11	52
127	Monolayer Molybdenum Disulfide Transistors with Single-Atom-Thick Gates. *Nano Letters*, **2018**, 18, 3807-3813	11.5	52
126	Highly Oriented Monolayer Graphene Grown on a Cu/Ni(111) Alloy Foil. *ACS Nano*, **2018**, 12, 6117-6127	16.7	100
125	Fermi Level Pinning at Electrical Metal Contacts of Monolayer Molybdenum Dichalcogenides. *ACS Nano*, **2017**, 11, 1588-1596	16.7	379
124	Controlled Folding of Single Crystal Graphene. *Nano Letters*, **2017**, 17, 1467-1473	11.5	60
123	High Electric Field Carrier Transport and Power Dissipation in Multilayer Black Phosphorus Field Effect Transistor with Dielectric Engineering. *Advanced Functional Materials*, **2017**, 27, 1604025	15.6	37
122	Electrically Driven Reversible Phase Changes in Layered In Se Crystalline Film. *Advanced Materials*, **2017**, 29, 1703568	24	45
121	Removal of Plasma-Induced Physical Damage Formed in Nanoscale Three-Dimensional FinFETs. *Nano*, **2017**, 12, 1750099	1.1	0
120	Modulation of Quantum Tunneling via a Vertical Two-Dimensional Black Phosphorus and Molybdenum Disulfide p-n Junction. *ACS Nano*, **2017**, 11, 9143-9150	16.7	113
119	Hydrogen-Induced Damage During the Plasma Etching Process. *Nano*, **2017**, 12, 1750112	1.1	
118	Carrier-Type Modulation and Mobility Improvement of Thin MoTe. *Advanced Materials*, **2017**, 29, 1606433	24	111
117	Organic Dye Graphene Hybrid Structures with Spectral Color Selectivity. *Advanced Functional Materials*, **2016**, 26, 6593-6600	15.6	25
116	Effects of plasma treatment on surface properties of ultrathin layered MoS 2. *2D Materials*, **2016**, 3, 035002	7.9	41
115	P-Type Polar Transition of Chemically Doped Multilayer MoS2 Transistor. *Advanced Materials*, **2016**, 28, 2345-51	24	141

114	Passivated ambipolar black phosphorus transistors. *Nanoscale*, **2016**, 8, 12773-9	7.7	70
113	Formation of PtSi Schottky barrier MOSFETs using plasma etching. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2015**, 33, 021307	2.9	4
112	Ultimate thin vertical p-n junction composed of two-dimensional layered molybdenum disulfide. *Nature Communications*, **2015**, 6, 6564	17.4	231
111	Carrier transport at the metal-MoS2 interface. *Nanoscale*, **2015**, 7, 9222-8	7.7	71
110	Self-screened high performance multi-layer MoS□ transistor formed by using a bottom graphene electrode. *Nanoscale*, **2015**, 7, 19273-81	7.7	27
109	Edge contacts of graphene formed by using a controlled plasma treatment. *Nanoscale*, **2015**, 7, 825-31	7.7	44
108	High-performance perovskite-graphene hybrid photodetector. *Advanced Materials*, **2015**, 27, 41-6	24	651
107	High carrier mobility in Si-MOSFETs with a hexagonal boron nitride buffer layer. *Solid State Communications*, **2015**, 209-210, 1-4	1.6	6
106	Metal-semiconductor barrier modulation for high photoresponse in transition metal dichalcogenide field effect transistors. *Scientific Reports*, **2014**, 4, 4041	4.9	85
105	High performance vertical tunneling diodes using graphene/hexagonal boron nitride/graphene hetero-structure. *Applied Physics Letters*, **2014**, 104, 053103	3.4	30
104	A new mussel-inspired polydopamine phototransistor with high photosensitivity: signal amplification and light-controlled switching properties. *Chemical Communications*, **2014**, 50, 1458-61	5.8	71
103	Unraveling Oxygen Transfer at the Graphene Oxide□ZnO Nanorod Interface. *Journal of Physical Chemistry C*, **2014**, 118, 17638-17642	3.8	17
102	Lateral MoS2 p-n junction formed by chemical doping for use in high-performance optoelectronics. *ACS Nano*, **2014**, 8, 9332-40	16.7	419
101	High-performance photocurrent generation from two-dimensional WS2 field-effect transistors. *Applied Physics Letters*, **2014**, 104, 193113	3.4	72
100	Reduction of metal contact resistance of graphene devices via CO2 cluster cleaning. *Applied Physics Letters*, **2014**, 104, 223110	3.4	27
99	Highly stretchable piezoelectric-pyroelectric hybrid nanogenerator. *Advanced Materials*, **2014**, 26, 765-9	24	382
98	Hybrid energy harvester based on nanopillar solar cells and PVDF nanogenerator. *Nanotechnology*, **2013**, 24, 175402	3.4	34
97	Flexible and transparent MoS2 field-effect transistors on hexagonal boron nitride-graphene heterostructures. *ACS Nano*, **2013**, 7, 7931-6	16.7	800

96	Integral control for synchronization of complex dynamical networks with unknown non-identical nodes. *Applied Mathematics and Computation*, **2013**, 224, 140-149	2.7	19
95	Controlled charge trapping by molybdenum disulphide and graphene in ultrathin heterostructured memory devices. *Nature Communications*, **2013**, 4, 1624	17.4	504
94	Modified write-and-verify scheme for improving the endurance of multi-level cell phase-change memory using Ge-doped SbTe. *Solid-State Electronics*, **2012**, 76, 67-70	1.7	3
93	Si-compatible cleaning process for graphene using low-density inductively coupled plasma. *ACS Nano*, **2012**, 6, 4410-7	16.7	77
92	High photocurrent and quantum efficiency of graphene photodetector using layer-by-layer stack structure and trap assistance **2012**,		1
91	Optoelectronic Performance of Radial-Junction Si Nanopillar and Nanohole Solar Cells. *IEEE Transactions on Electron Devices*, **2012**, 59, 2368-2374	2.9	14
90	Enhancement of light absorption using high-k dielectric in localized surface plasmon resonance for silicon-based thin film solar cells. *Journal of Applied Physics*, **2011**, 109, 093516	2.5	10
89	. *IEEE Transactions on Electron Devices*, **2011**, 58, 3254-3259	2.9	3
88	. *IEEE Transactions on Electron Devices*, **2011**, 58, 3321-3328	2.9	0
87	Multi-level cell storage with a modulated current method for phase-change memory using Ge-doped SbTe. *Current Applied Physics*, **2011**, 11, e79-e81	2.6	6
86	Plasma treatments to improve metal contacts in graphene field effect transistor. *Journal of Applied Physics*, **2011**, 110, 073305	2.5	48
85	Self-Assembled Wire Arrays and ITO Contacts for Silicon Nanowire Solar Cell Applications. *Chinese Physics Letters*, **2011**, 28, 035202	1.8	9
84	Temperature of a Semiconducting Substrate Exposed to an Inductively Coupled Plasma. *Journal of the Korean Physical Society*, **2011**, 59, 262-270	0.6	3
83	. *IEEE Transactions on Electron Devices*, **2010**, 57, 2794-2800	2.9	5
82	Deep level transient spectroscopy on charge traps in high-k ZrO2. *Thin Solid Films*, **2010**, 518, 6382-6384	2.2	7
81	Pulse-agitated self-convergent programming for 4-bit per cell dual charge storage layer flash memory. *Solid-State Electronics*, **2010**, 54, 14-17	1.7	5
80	Localized Surface Plasmon Resonances by Ag Nanoparticles on SiN for Solar Cell Application. *Journal of the Korean Physical Society*, **2010**, 56, 1488-1491	0.6	12
79	Dual phase TiO(x)N(y)/TiN charge trapping layer for low-voltage and high-speed flash memory application. *Journal of Nanoscience and Nanotechnology*, **2009**, 9, 7446-50	1.3	

78	Second-Bit-Effect-Free Multibit-Cell Flash Memory Using $hbox{Si}_{3} hbox{N}_{4}/hbox{ZrO}_{2}$ Split Charge Trapping Layer. *IEEE Transactions on Electron Devices*, **2009**, 56, 1966-1973	2.9	2
77	$V_{rm th}$ Control by Complementary Hot-Carrier Injection for SONOS Multi-Level Cell Flash Memory. *IEEE Transactions on Electron Devices*, **2009**, 56, 3027-3032	2.9	3
76	Effects of Nanostructures Formed by Plasma Etching on the Reflectance of Solar Cells. *Journal of the Korean Physical Society*, **2009**, 54, 1016-1020	0.6	4
75	Frequency and Temperature Dependence of the Dielectric Properties of a PCB Substrate for Advanced Packaging Applications. *Journal of the Korean Physical Society*, **2009**, 54, 1096-1099	0.6	19
74	Roles of F and O Radicals and Positive Ions in a SF6/O2 Plasma in Forming Deep Via Structures. *Journal of the Korean Physical Society*, **2009**, 54, 1774-1778	0.6	7
73	Application of the Black Silicon Phenomenon to Forming High-Aspect-Ratio Deep Vias. *Journal of the Korean Physical Society*, **2009**, 54, 616-620	0.6	2
72	Hot-Electron Capture for CHEI Programming in SONOS-Type Flash Memory Using High- k Trapping Layer. *IEEE Transactions on Electron Devices*, **2008**, 55, 1502-1510	2.9	12
71	Endurance Reliability of Multilevel-Cell Flash Memory Using a $ hbox{ZrO}_{2}/hbox{Si}_{3}hbox{N}_{4}$ Dual Charge Storage Layer. *IEEE Transactions on Electron Devices*, **2008**, 55, 2361-2369	2.9	11
70	Effects of Volatility of Etch By-products on Surface Roughness During Etching of Metal Gates in Cl[sub 2]. *Journal of the Electrochemical Society*, **2008**, 155, H6	3.9	9
69	SELF-ASSEMBLY OF Si NANOSTRUCTURES IN SF6/O2 PLASMA. *Nano*, **2008**, 03, 169-173	1.1	6
68	A time-dependent technique for carrier recombination and generation lifetime measurement in SOI MOSFET. *Solid-State Electronics*, **2008**, 52, 1773-1777	1.7	1
67	Novel ZrO2/Si3N4 Dual Charge Storage Layer to Form Step-Up Potential Wells for Highly Reliable Multi-Level Cell Application **2007**,		3
66	Electrical Characteristics of Memory Devices With a High- k $hbox{HfO}_{2}$ Trapping Layer and Dual $hbox{SiO}_{2}/hbox{Si}_{3}hbox{N}_{4}$ Tunneling Layer. *IEEE Transactions on Electron Devices*, **2007**, 54, 2699-2705	2.9	38
65	Partial Crystallization of $hbox{HfO}_{2}$ for Two-Bit/Four-Level SONOS-Type Flash Memory. *IEEE Transactions on Electron Devices*, **2007**, 54, 3177-3185	2.9	12
64	Spatial Distribution of Charge Traps in a SONOS-Type Flash Memory Using a High- k Trapping Layer. *IEEE Transactions on Electron Devices*, **2007**, 54, 3317-3324	2.9	45
63	Sub-30 nm Strained p-Channel Fin-Type Field-Effect Transistors with Condensed SiGe Source/Drain Stressors. *Japanese Journal of Applied Physics*, **2007**, 46, 2058-2061	1.4	8
62	Low energy N2 ion bombardment for removal of (HfO2)x(SiON)1 in dilute HF. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2007**, 25, 1056-1061	2.9	2
61	. *IEEE Transactions on Semiconductor Manufacturing*, **2007**, 20, 143-149	2.6	16

60	Integrated process of photoresist trimming and dielectric hard mask etching for sub-50 nm gate patterning. *Thin Solid Films*, **2006**, 504, 117-120	2.2	1
59	Effects of SiO2Si3N4 hard masks on etching properties of metal gates. *Journal of Vacuum Science & Technology B*, **2006**, 24, 2689		9
58	Investigation of Wet Etching Properties and Annealing Effects of Hf-Based High-k Materials. *Journal of the Electrochemical Society*, **2006**, 153, G483	3.9	11
57	Effects of N2, O2, and Ar plasma treatments on the removal of crystallized HfO2 film. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2006**, 24, 133-140	2.9	6
56	Drive-Current Enhancement in FinFETs Using Gate-Induced Stress. *IEEE Electron Device Letters*, **2006**, 27, 769-771	4.4	10
55	Novel HfAlO charge trapping layer in SONOS type flash memory for multi-bit per cell operation **2006**,		1
54	Rapid thermal oxidation of Ge-rich Si1Gex heterolayers. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2006**, 24, 84-90	2.9	7
53	Fast erasing and highly reliable MONOS type memory with HfO2 high-k trapping layer and Si3N4/SiO2 tunneling stack **2006**,		9
52	Chemically Assisted Formation of Nanocrystals for Micro-electronics Application. *Studies in Surface Science and Catalysis*, **2006**, 73-78	1.8	
51	Chemical analysis of etching residues in metal gate stack for CMOS process. *Studies in Surface Science and Catalysis*, **2006**, 159, 365-368	1.8	2
50	Simulation of trapping properties of high material as the charge storage layer for flash memory application. *Thin Solid Films*, **2006**, 504, 209-212	2.2	3
49	Formation of dual-phase HfO2HfxSi1O2 dielectric and its application in memory devices. *Journal of Applied Physics*, **2005**, 98, 013536	2.5	16
48	Three-dimensional metal gate-high-/spl kappa/-GOI CMOSFETs on 1-poly-6-metal 0.18-n Si devices. *IEEE Electron Device Letters*, **2005**, 26, 118-120	4.4	25
47	Low noise RF MOSFETs on flexible plastic substrates. *IEEE Electron Device Letters*, **2005**, 26, 489-491	4.4	13
46	Effect of porosity on electrical stability of hydrocarbon polymeric low-k dielectric. *IEEE Transactions on Electron Devices*, **2005**, 52, 2333-2336	2.9	9
45	Impact of buried capping layer on electrical stability of advanced interconnectsa). *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 1499		0
44	Self-assembled tungsten nanocrystals in high-k dielectric for nonvolatile memory application. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 2278		12
43	Effect of electric field on chemical bonds of carbon-doped silicon oxide as evidenced by in situ Fourier transform infrared spectroscopy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2005**, 23, 433		4

42	Investigation of etching properties of metal nitride/high-k gate stacks using inductively coupled plasma. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2005**, 23, 964-970	2.9	51
41	Tungsten nanocrystals embedded in high-k materials for memory application. *Applied Physics Letters*, **2005**, 87, 113110	3.4	49
40	Self-assembly of Ni nanocrystals on HfO2 and N-assisted Ni confinement for nonvolatile memory application. *Applied Physics Letters*, **2005**, 86, 013107	3.4	61
39	Self-assembly of Al2O3 nanodots on SiO2 using two-step controlled annealing technique for long retention nonvolatile memories. *Applied Physics Letters*, **2005**, 86, 073114	3.4	33
38	A novel program-erasable high-/spl kappa/ AlN-Si MIS capacitor. *IEEE Electron Device Letters*, **2005**, 26, 148-150	4.4	13
37	Investigation of etching properties of HfO based high-K dielectrics using inductively coupled plasma. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2004**, 22, 1552-1558	2.9	36
36	Formation of SiGe nanocrystals in HfO2 using in situ chemical vapor deposition for memory applications. *Applied Physics Letters*, **2004**, 84, 4331-4333	3.4	25
35	Effects of Annealing and Ar Ion Bombardment on the Removal of HfO[sub 2] Gate Dielectric. *Electrochemical and Solid-State Letters*, **2004**, 7, F18		14
34	Chemical Vapor Deposition of Germanium Nanocrystals on Hafnium Oxide for Non-Volatile Memory Applications. *Materials Research Society Symposia Proceedings*, **2004**, 830, 299		1
33	Nonvolatile flash memory device using Ge nanocrystals embedded in HfAlO high-/spl kappa/tunneling and control oxides: Device fabrication and electrical performance. *IEEE Transactions on Electron Devices*, **2004**, 51, 1840-1848	2.9	90
32	Schottky-barrier S/D MOSFETs with high-k gate dielectrics and metal-gate electrode. *IEEE Electron Device Letters*, **2004**, 25, 268-270	4.4	83
31	Enhancement of adhesion strength of Cu layer on single and multi-layer dielectric film stack in Cu/low k multi-level interconnects. *Microelectronic Engineering*, **2004**, 75, 183-193	2.5	5
30	Study of leakage mechanisms of the copper/Black Diamond damascene process. *Thin Solid Films*, **2004**, 462-463, 330-333	2.2	12
29	Low temperature MOSFET technology with Schottky barrier source/drain, high-K gate dielectric and metal gate electrode. *Solid-State Electronics*, **2004**, 48, 1987-1992	1.7	26
28	Direct trim etching process of Si/SiO2 gate stacks using 193 nm ArF patterns. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2004**, 22, 1500-1505	2.9	1
27	Formation of Ge nanocrystals in HfAlO high-k dielectric and application in memory device. *Applied Physics Letters*, **2004**, 84, 5407-5409	3.4	47
26	Formation of polycrystalline silicon germanium/HfO2 gate stack structure using inductively coupled plasma etching. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2003**, 21, 1210-1217	2.9	10
25	Investigation of electrical conduction in carbon-doped silicon oxide using a voltage ramp method. *Applied Physics Letters*, **2003**, 83, 524-526	3.4	45

24	Investigation of in situ trench etching process and Bosch process for fabricating high-aspect-ratio beams for microelectromechanical systems. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 1878		21
23	In situ trench etching and releasing technique of high aspect ratio beams using magnetically enhanced reactive ion etching. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 154		5
22	Effects of Poly-Si Annealing on Gate Oxide Charging Damage in Poly-Si Gate Etching Process. *Materials Research Society Symposia Proceedings*, **2002**, 716, 4161		
21	Plasma Etching Techniques to Form High-Aspect-Ratio MEMS Structures. *Microsystems*, **2002**, 273-294		
20	RHEED AND XPS STUDIES OF THE DECOMPOSITION OF SILICON DIOXIDE BY THE BOMBARDMENT OF METAL IONS. *Surface Review and Letters*, **2001**, 08, 521-526	1.1	
19	Crystalline zirconia oxide on silicon as alternative gate dielectrics. *Applied Physics Letters*, **2001**, 78, 1604-1606	3.4	82
18	Electrical properties of crystalline YSZ films on silicon as alternative gate dielectrics. *Semiconductor Science and Technology*, **2001**, 16, L13-L16	1.8	30
17	High temperature platinum etching using Ti mask layer. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 2151-2155	2.9	25
16	Anisotropic etching characteristics of platinum electrode for ferroelectric capacitor. *IEEE Transactions on Electron Devices*, **1999**, 46, 984-992	2.9	7
15	Effects of Conductivity of Polysilicon on Profile Distortion. *Japanese Journal of Applied Physics*, **1996**, 35, 2440-2444	1.4	16
14	Control of Etch Slope during Etching of Pt inAr/Cl2/O2Plasmas. *Japanese Journal of Applied Physics*, **1996**, 35, 2501-2504	1.4	61
13	Process-induced particle formation in the sputtering and reactive ion etching of silicon and silicon dioxide. *Plasma Sources Science and Technology*, **1994**, 3, 273-277	3.5	8
12	Mechanism of particle formation in the sputtering and reactive ion etching of Si and SiO2. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1994**, 12, 2758		3
11	Growth of plasma-generated particles and behavior of particle clouds during sputtering of silicon and silicon dioxide. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1993**, 11, 1258-1263	2.9	14
10	Kinetics of particle generation in sputtering and reactive ion etching plasmas. *Applied Physics Letters*, **1992**, 60, 1073-1075	3.4	14
9	Kinetics of particle formation in the sputtering and reactive ion etching of silicon. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1992**, 10, 1041-1047	2.9	17
8	Reactive Ion Etching of Copper with SiCl4 and CCl2F2. *Materials Research Society Symposia Proceedings*, **1990**, 201, 129		2
7	Enhancement of memory window in short channel non-volatile memory devices using double layer tungsten nanocrystals		20

6	Reliability improvement using buried capping layer in advanced interconnects		5
5	3D GOI CMOSFETs with novel IrO/sub 2/(Hf) dual gates and high-k dielectric on 1P6M-0.18 /spl mu/m-CMOS		10
4	Lanthanide and Ir-based dual metal-gate/HfAlON CMOS with large work-function difference		16
3	Contact Resistivity in Edge-Contacted Graphene Field Effect Transistors. *Advanced Electronic Materials*,2101169	6.4	1
2	Chemical Dopant-Free Doping by Annealing and Electron Beam Irradiation on 2D Materials. *Advanced Electronic Materials*,2100449	6.4	5
1	Metal□nsulator Transition Driven by Traps in 2D WSe 2 Field-Effect Transistor. *Advanced Electronic Materials*,2200046	6.4	3